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Kind regards,

Team Nexperia



PSMN6R3-120PS

N-channel 120 V 6.7 mΩ standard level MOSFET in TO-220

7 June 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic power supply equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive
- TO-220 package can be mounted to heatsink

3. Applications

- AC-to-DC power supply
- Synchronous rectification
- Motor control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25 \text{ }^\circ\text{C}; T_j \leq 175 \text{ }^\circ\text{C}$		-	-	120	V
I_D	drain current	$T_{mb} = 25 \text{ }^\circ\text{C}; V_{GS} = 10 \text{ V};$ Fig. 1		-	-	70	A
P_{tot}	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C};$ Fig. 2		-	-	405	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 12		4	5.7	6.7	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 60 \text{ V};$ Fig. 14 ; Fig. 15		-	61.9	-	nC
$Q_{G(tot)}$	total gate charge			-	207.1	-	nC
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ }^\circ\text{C}; I_D = 70 \text{ A}; V_{sup} \leq 120 \text{ V};$ unclamped; $R_{GS} = 50 \Omega;$ Fig. 3		-	-	532	mJ

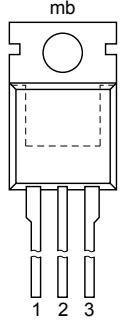
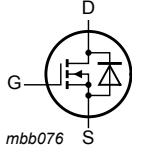


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	drain	 TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package			Version
	Name	Description	Version	
PSMN6R3-120PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78	

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25^\circ\text{C}$; $T_j \leq 175^\circ\text{C}$	-	120	V
V_{DGR}	drain-gate voltage	$T_j \geq 25^\circ\text{C}$; $T_j \leq 175^\circ\text{C}$; $R_{GS} = 20\text{ k}\Omega$	-	120	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25^\circ\text{C}$; Fig. 1	-	70	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100^\circ\text{C}$; Fig. 1	-	70	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25^\circ\text{C}$; Fig. 4	-	280	A
P_{tot}	total power dissipation	$T_{mb} = 25^\circ\text{C}$; Fig. 2	-	405	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25^\circ\text{C}$	-	70	A

Symbol	Parameter	Conditions	Min	Max	Unit
I_{SM}	peak source current	pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$	-	280	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}$; $T_{j(\text{init})} = 25^\circ\text{C}$; $I_D = 70 \text{ A}$; $V_{sup} \leq 120 \text{ V}$; unclamped; $R_{GS} = 50 \Omega$; Fig. 3	-	532	mJ

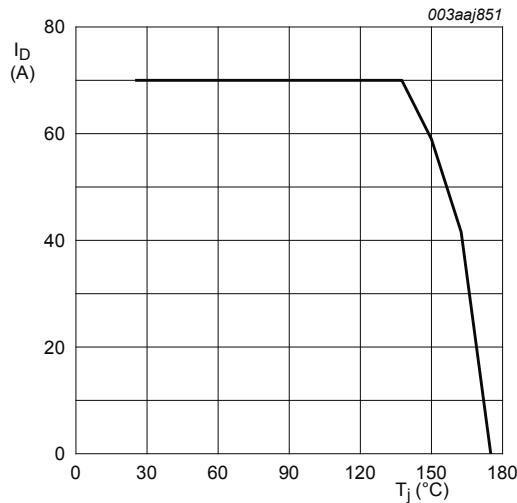


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10 \text{ V}$$

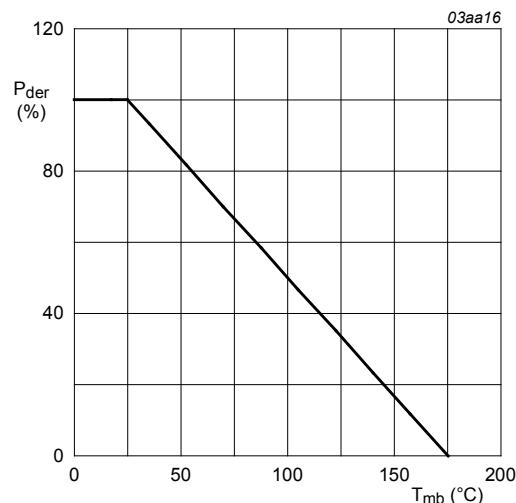


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot}(25^\circ\text{C})} \times 100 \%$$

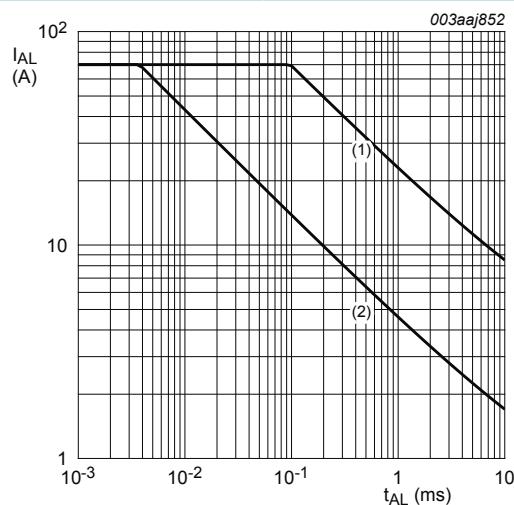


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

(1) Single-pulse; $T_j = 25^\circ\text{C}$.

(2) Single-pulse; $T_j = 125^\circ\text{C}$.

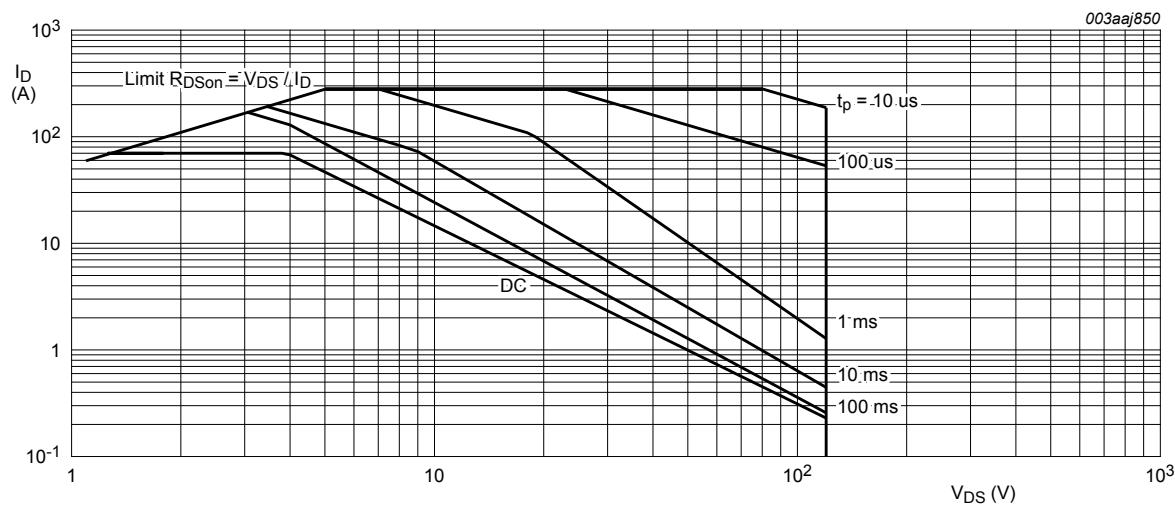


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

 $T_{mb} = 25^\circ C$; I_{DM} is single pulse

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.3	0.37	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

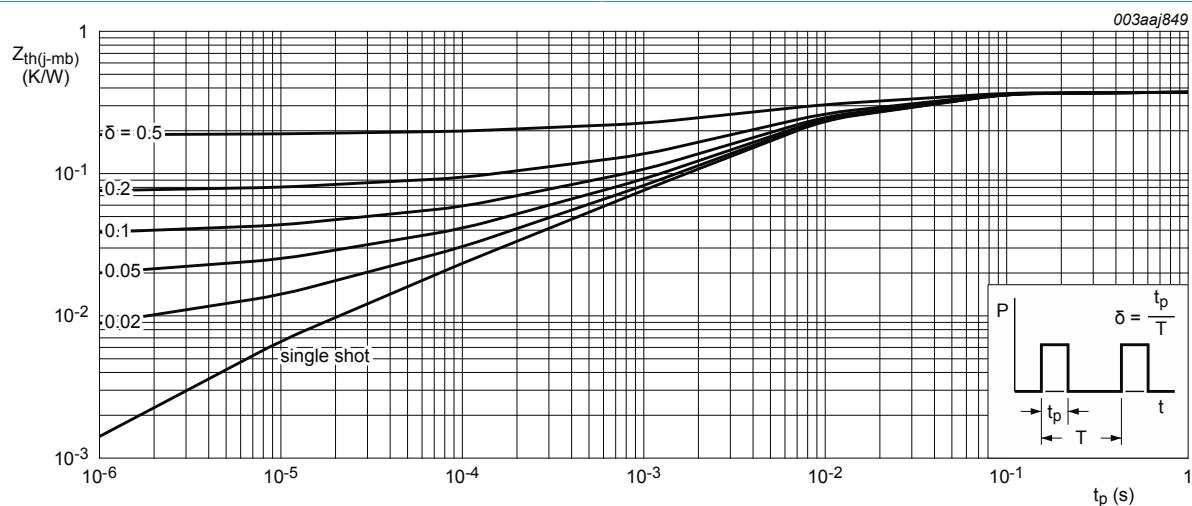


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		120	-	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C		108	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10 ; Fig. 11		2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10 ; Fig. 11		1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10 ; Fig. 11		-	-	4.6	V
I _{DSS}	drain leakage current	V _{DS} = 120 V; V _{GS} = 0 V; T _j = 25 °C		-	0.1	1	μA
		V _{DS} = 120 V; V _{GS} = 0 V; T _j = 175 °C		-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C		-	10	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12		4	5.7	6.7	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 13 ; Fig. 12		-	16.5	19.4	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz		0.44	0.88	1.76	Ω
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 60 V; V _{GS} = 10 V; Fig. 14 ; Fig. 15		-	207.1	-	nC
Q _{GS}	gate-source charge			-	43.2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge			-	29.8	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge			-	13.4	-	nC
Q _{GD}	gate-drain charge			-	61.9	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 60 V; Fig. 14 ; Fig. 15		-	4.3	-	V
C _{iss}	input capacitance	V _{DS} = 60 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 16		-	11384	-	pF
C _{oss}	output capacitance			-	534	-	pF
C _{rss}	reverse transfer capacitance			-	358	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω; T _j = 25 °C		-	42.1	-	ns
t _r	rise time			-	58.2	-	ns

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$t_{d(\text{off})}$	turn-off delay time		-	-	142.1	-	ns
t_f	fall time		-	-	67.7	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25^\circ\text{C}$; Fig. 17	-	-	0.79	1.2	V
t_{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A}/\mu\text{s}$; $V_{GS} = 0 \text{ V}$	-	-	76.1	-	ns
Q_r	recovered charge	$V_{DS} = 60 \text{ V}$	-	-	264.2	-	nC

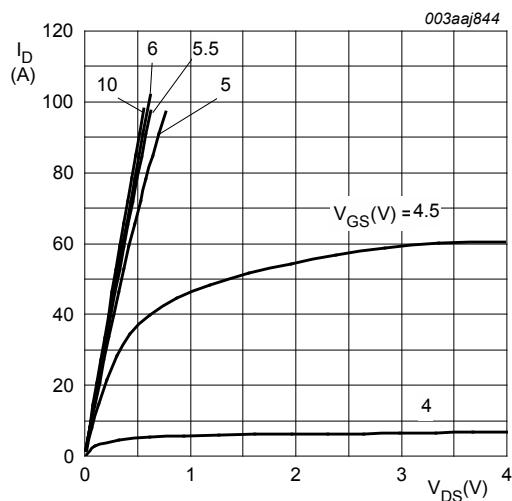


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

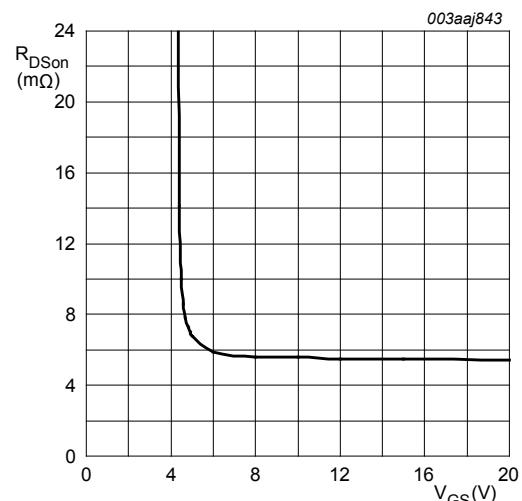


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}$

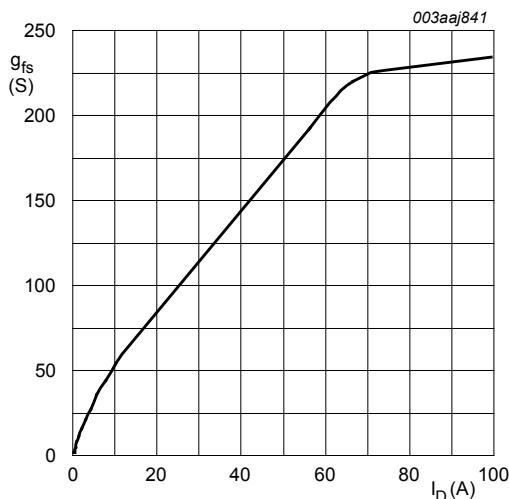


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 10 \text{ V}$

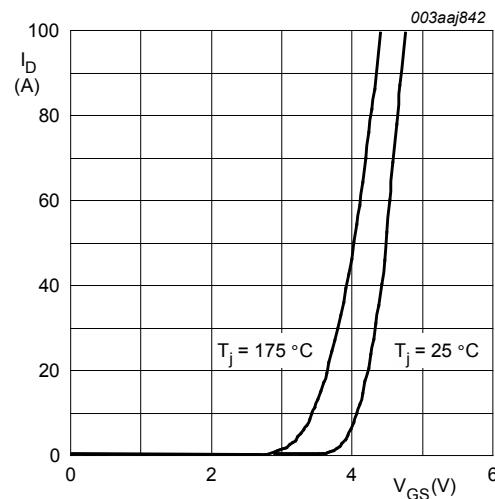


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} > I_D \times R_{DS(on)}$

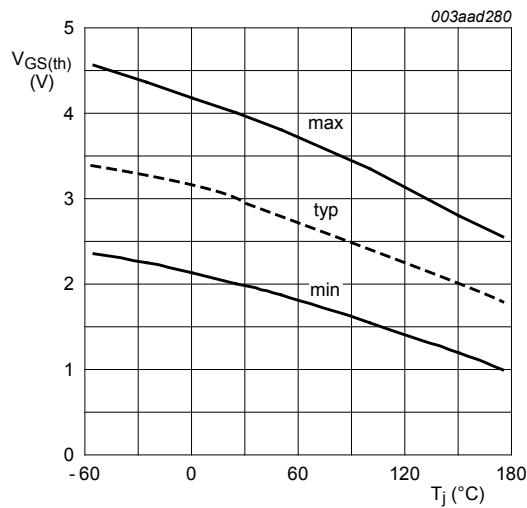


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

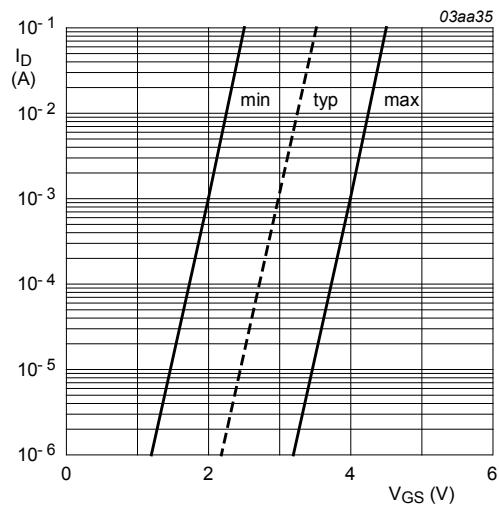


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

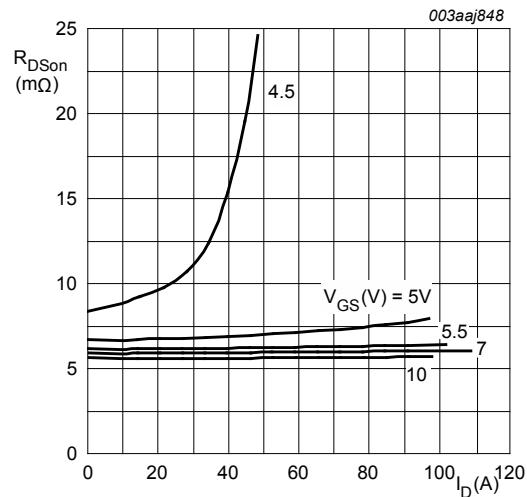


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^\circ\text{C}$$

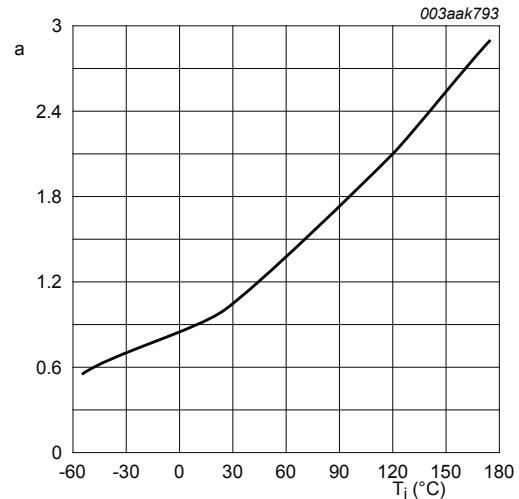


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

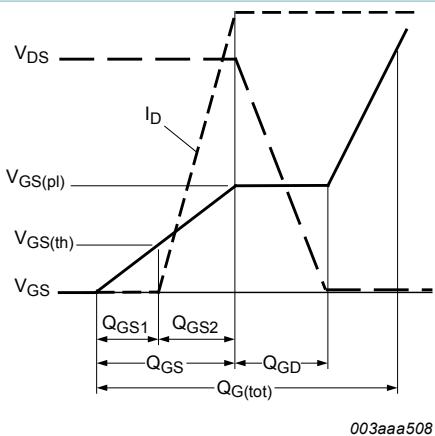


Fig. 14. Gate charge waveform definitions

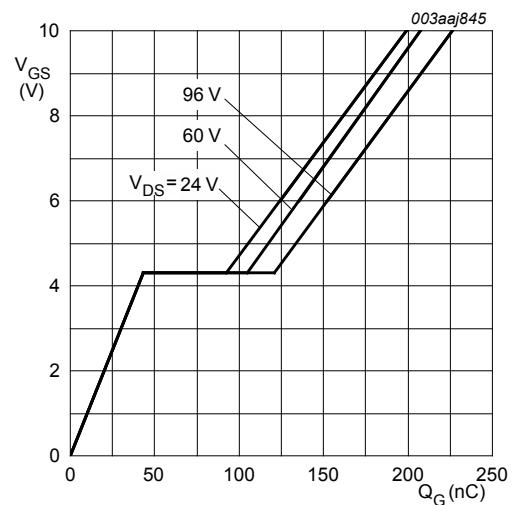


Fig. 15. Gate-source voltage as a function of gate charge; typical values

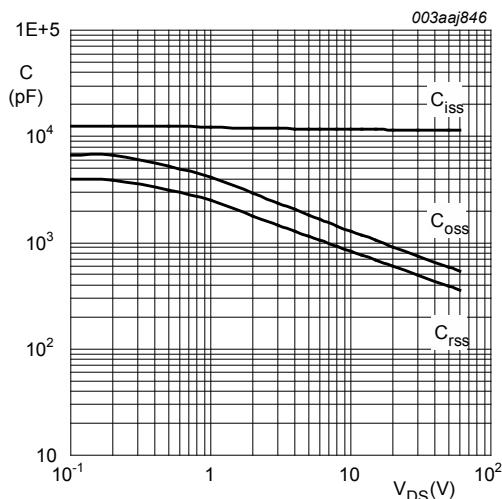
 $T_j = 25^\circ\text{C}; I_D = 25\text{ A}$ 

Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

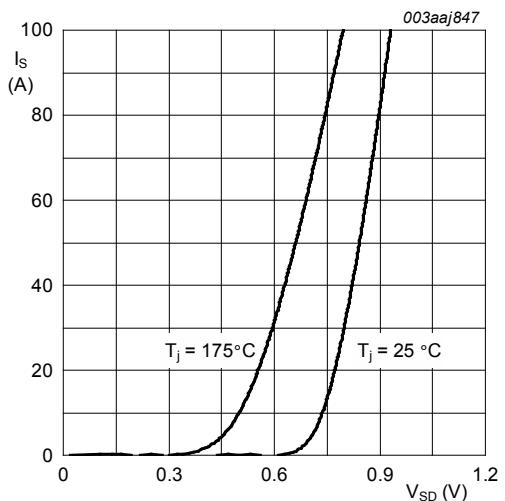
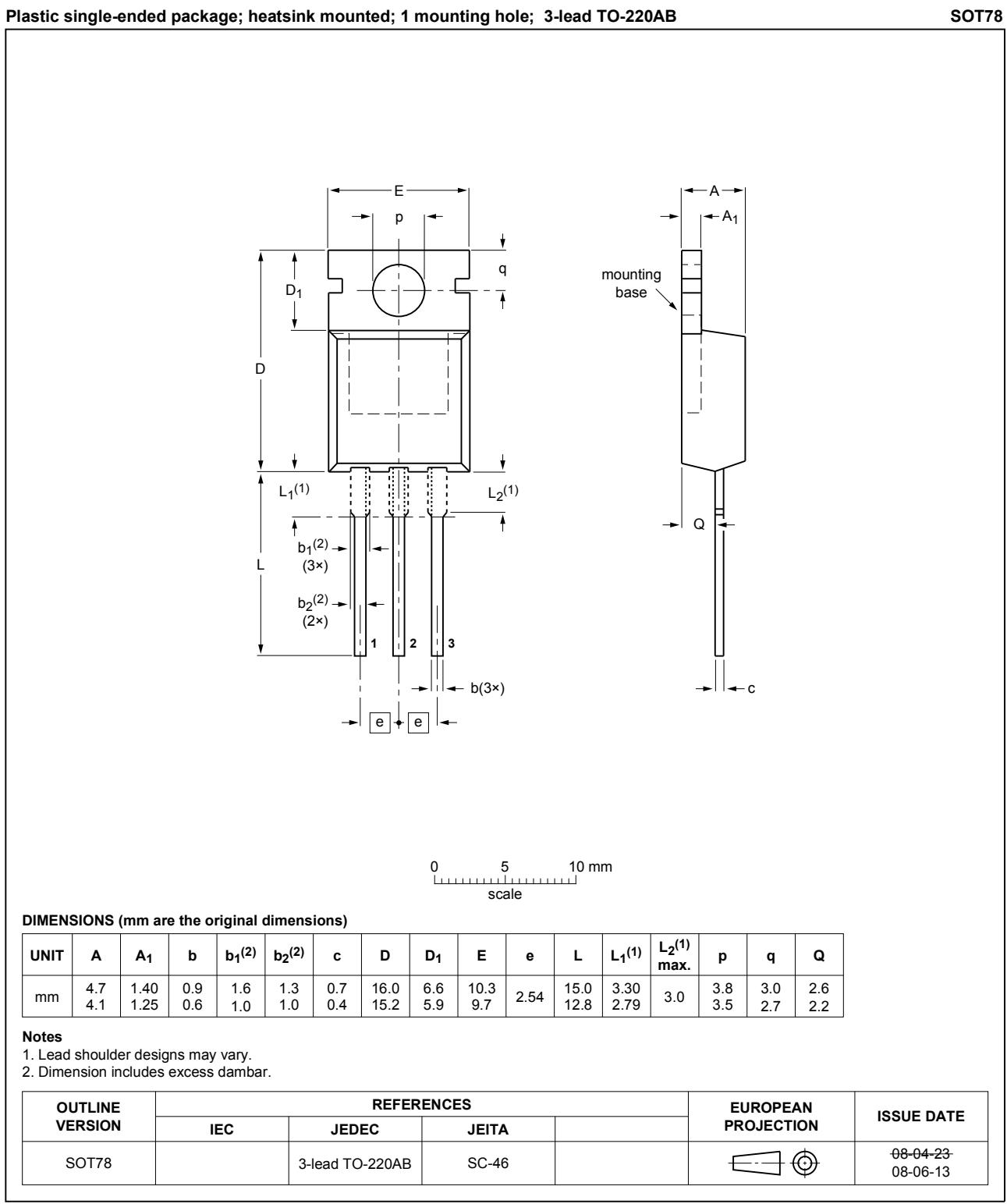
 $V_{GS} = 0\text{ V}; f = 1\text{ MHz}$ 

Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

 $V_{GS} = 0\text{ V}$

10. Package outline



11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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